Abstracts

A 1-157 GHz InP HEMT traveling-wave amplifier

B. Agarwal, A.E. Schmitz, J.J. Brown, M. Le, M. Lui and M.J.W. Rodwell. "A 1-157 GHz InP HEMT traveling-wave amplifier." 1998 Radio Frequency Integrated Circuits (RFIC) Symposium 98. (1998 [RFIC]): 21-23.

We report traveling wave amplifiers with 1-157 GHz 3-dB bandwidth, 5 dB gain. These amplifiers were fabricated in a 0.1 /spl mu/m gate length InGaAs/InAlAs HEMT MMIC technology. The use of gate-line capacitive-division and low-loss elevated coplanar waveguide lines have yielded record bandwidth broadband amplifiers.

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